

24.7500

36794

S/137/62/000/004/053/201

A052/A101

AUTHORS: Kokorish, Ye. Yu., Sheftal', N. N.

TITLE: On the problem of growth of dislocationless germanium single crystals

PERIODICAL: Referativnyy zhurnal, Metallurgiya, no. 4, 1962, 48, abstract 40320  
(V. sb. "Rost kristallov. T. 3". Moscow, AN SSSR, 1961, 388 - 394.  
Discuss., 501 - 502)

TEXT: The effect of some parameters of growing by Chokhral'skiy method on the formation of dislocations in Ge single crystals was studied. As initial material polycrystalline Ge ingots, purified by zone melting, with specific resistance of  $> 30$  ohm-cm were used. The diameter of single crystals varied from 6 to 30 mm. The rate of extraction was constant or changed according to the set program from 4 to 0.5 mm/min. The rotating speed of the seed crystal was 50 - 100 rpm, the direction of growing was [111]. The density of dislocations was determined by pickling pits which were detected in the [111] plane, after pickling in potassium ferricyanide solution. It is shown that the density of dislocations in the speed range of 0.5 - 3 mm/min does not depend practically on the rate of extraction and is determined mainly by the cooling conditions of the crystal. At

Card 1/3

On the problem of growth of...

S/137/62/000/004/053/201  
A052/A101

rates of extraction of  $> 4$  mm/min a noticeable increase in the density of dislocations is observed. The effect of the diameter on the density of dislocations was studied at a rate of extraction of 1 mm/min. It is established that with the increase of dimensions of the crystal the density of dislocations increases which is conditioned by considerable difficulties connected with the cooling of large-size crystals. No noticeable effect of Sb, Bi, Ga and In admixtures as well as of a different orientation of seed crystals in [111], [110] and [100] directions on the density of dislocations in the grown crystals was detected. The main part in the formation of dislocations in Ge single crystals play the cooling conditions of the growing crystal from the crystallization temperature to the indoor temperature, and also the perfection degree of the seed crystal. To eliminate considerable temperature gradients in the process of extraction, it is necessary to heat additionally the growing crystal and to cool down very slowly. When a special graphite crucible with a screen was used, the value of the axial temperature gradient on the surface of the crystal was 20 - 40 deg/cm with the resulting decrease of the density of dislocations to  $10 \text{ cm}^{-2}$  and lower. Dislocationless single crystals were produced at extraction with a seed crystal having no dislocations or with a density lower than  $10^3 \text{ cm}^{-2}$ . The end of the seed crystal immersed in the smelt had a cone-shaped form. At the beginning a thin crystal was grown. High- and

Card 2/3

S/137/62/000/004/053/201  
A052/A101

On the problem of growth of...

low-resistance dislocationless single crystals weighing up to 40 g were produced. Dislocationless crystals as well as crystals with a small density of dislocations had usually higher values of diffusion length than crystals with a density of dislocations of  $10^5 \text{ cm}^{-2}$  and more. Ge single crystals with a small density of dislocations were produced at zone melting with the temperature gradient of  $15^\circ\text{C}$  after the fused zone at its rate of displacement of 2 mm/min. It is established that the dislocations in Ge single crystal arise mainly in the process of its cooling from high temperatures to  $< 500^\circ\text{C}$  and as a partial spreading from the seed crystal.

B. Turovskiy

[Abstracter's note: Complete translation]

Card 3/3

OZOLS, K.K.; KOKORISH, Ye. Iu.

Synthesis of gallium arsenide single crystals. Rost krist. 4:  
181-202 '64. (MIRA 17:8)

LACKOVA, E.; MOVAKOVA, M.; KOKORNA, M.; SVEJCAR, J.

Our experience with the measurement of children by means of  
Lelong's method. Cesk.pediat. 15 no.8:669-677 Ag '60.

1. I detska klinika v Praze, prednosta prof. MUDr. J.Svejcar  
(ANTHROPOMETRY)  
(GROWTH)

KOKORNA, Vera, dr.

Values of water retention and of ashes in various types of peat  
in various localities. *Fysiat.vest.*, Praha 33 no.6:207-216 Dec 55.

L. Vyznamy ~~metod~~ ~~laboratorni~~ ~~prace~~ ~~pevnosti~~ ~~pevnosti~~ ~~pevnosti~~  
(PEAT, water retention & ashes)

KOKOROVILI, G., inzh.

Equipment for testing air bottles. Avt. transp. 43 no.8:42-43  
Ag '65. (MIRA 18:9)

1. KOKOROV, V. I., Eng.

2. USSR (600)

4. Lumbering

7. Self-releasing choker for stacking lumber with winches. Les. prom. 12 no. 12 1952.

9. Monthly List of Russian Accessions, Library of Congress, March 1953. Unclassified.



KOKORYSHKIN, V.N.

Heat treatment of disk springs. Mashinostroitel' no.12:26 F '63.  
(MIRA 16:3)

(Springs (Mechanism))

(Steel—Heat treatment)

ZHAVRID, V.M.; MATVEYKOV, G.P.; KOKOSH, A.A.

Changes in the cardiocascular system in chronic tonsil-  
litis. Zdrav. Bel. 8 no.6:10-12 Je'62. (MIRA 16:8)

1. Iz kafedry gosptal'noy terapii (zav. - prof. G.Kh.  
Dovgyallo) Minskogo meditsinskogo instituta.  
(TONSILS—DISEASE) (CARDIOVASCULAR SYSTEM—DISEASES)

KOKOSH, G.D.

Photographic recording of balance swings. Trudy VNIIM no.2:25-  
30 '47. (MIRA 1241)  
(Balance) (Photography--Scientific applications)

KOKOSH, G.D.; MOROZOVA, I.N.

Weights made of quartz. Trudy VNIIM no.19:7-12 '52. (MIRA 11:6)  
(Weights and measures) (Quartz)

KOKOSH, G.D.; SMIRNOVA, N.A.

~~Applying~~ Applying the method of torsion pendulum in investigating balance  
arms of precision balances. Trudy VNIIM no.19:21-30 '52.  
(Balance) (MIRA 11:6)

KOKOSH, G. D.

"Investigation of Oscillations of Precision Balances." Dr Tech  
Sci, All-Union Sci Res Inst of Metrology; Leningrad Ship-building  
Inst, Leningrad, 1954. (RZhNekkh, Sep 54)

SO: Sum 432, 29 Mar 55

KOKOSH, G.D., kand. fiz.-mat. nauk.

Laws of changes of resistance forces and energy dissipation caused  
by the swinging of precision balances. Trudy VNIIM no. 27:5-22 '55.  
(Balance) (MIRA 11:6)

KOKOSH, G.D.

Selecting calculation formulas for the determination of swing  
centers of balance beams. Trudy VNIIM no.27:55-59 '55. (MIRA 11:6)  
(Balance)



RUDO, N.M., kand. tekhn. nauk; IPPITS, M.D., kand. tekhn. nauk;  
KOKOSH, G.D., kand. fiziko-matem. nauk.

[Instruction 58-54 for checking hydrostatic steelyard-  
type balances] Instruksiia 58-54 po poverke gidrostatiki-  
cheskikh vesov bezmennogo tipa. Izd. ofitsial'noe. Mo-  
skva, 1956. 15 p. (MIRA 14:5)

1. Russia (1923- U.S.S.R.) Komitet standartov, ser 1 iz-  
meritel'nykh priborov.

(Balance--Testing)

~~KOKOSH, G.D.~~  
KOKOSH, G.D., kand.fiziko-matem.nauk; IZMAYLOV, S.V., kand.fiz.-mat.nauk,  
nauchnyy red.; VLADIMIRSKIY, D.M., red.isd-va; GURDZHIEVA, A.M.,  
tekhn.red.

[Atomnaya energiya v prirode. Leningrad, Ob-vo po rasprostraneniю  
polit.i nauchn.znaniy BSPSR, Leningr.otd-nie, 1957. 37 p. (MIRA 11:1)  
(Atomic energy)]

*KOKOSH, G.D.*

HUDO, Nikolay Mikhaylovich, kand.tekhn.nauk; GULIN, G.A., inzh.,  
retsensent; ~~KOKOSH, G.D.~~, kand. fiz.-mat.nauk, red.; GOFMAN, Ye.K.,  
red.isd-va; SOKOLOVA, L.V., tekhn.red.

[Scales; theory, operation, regulation and checking] Vesny;  
teoriia, ustroistvo, regulirovka i poverka. Moskva, Gos.nauchno-  
tekhn.isd-vo mashinostroit.lit-ry, 1957. 350 p. (MIRA 11:1)  
(Scales (Weighing instruments))



*Kokosh, G. V.*

Category: USSR / Physical Chemistry.

Thermodynamics. Thermochemistry. Equilibrium. Physico-chemical analysis. Phase transitions.

B-8

Abs Jour: Referat Zhur-Khimiya, No 9, 1957, 29930

Author : Shchukarev S. A., Morozova M. P., Kan Kho-Yu, Kokosh G. V.

Inst : not given

Title : Strontium-Bismuth System

Orig Pub: Zh. obshch. khimii, 1956, 26, No 6, 1525-1531

Abstract: By methods of physico-chemical analysis a study has been made of the Sr - Bi system. On the basis of thermal analysis data and distribution of averaged gram-atomic volumes, it was ascertained that there exist the congruent fusible compounds  $SrBi_2$ ,  $Sr_2Bi_3$  and  $Sr_3Bi_2$  and the incongruent fusible  $SrBi$ . Results of microscopic investigation confirm the type of the diagram of state derived by means of the first two methods. From values of thermal effect of interaction of  $SrBi$ ,  $Sr_2Bi_3$  and  $Sr_3Bi_2$  with dilute HCl (for description of the calorimetric procedure see RZhKhim, 1955, 34012) a determination was made of enthalpy

Card : 1/2

-45-

*Leningrad. Univ.*

Category: USSR / Physical Chemistry.

Thermodynamics. Thermochemistry. Equilibrium. Physico-chemical analysis. Phase transitions.

B-8

Abs Jour: Referat Zhur-Khimiya, No 9, 1957, 29930

of their formation,  $\Delta H$ , which was found to be, respectively, of  $-43.0 \pm 2.7$ ;  $-126.8 \pm 2.6$  and  $-74.8 \pm 1.2$  kcal/g-formula. A comparison is presented of the  $\Delta H$  values of some binary compounds of elements of principal subgroup of group V of the periodic system with alkaline-earth metals.

Card : 2/2

-46-

"APPROVED FOR RELEASE: 06/19/2000

CIA-RDP86-00513R000723710011-9

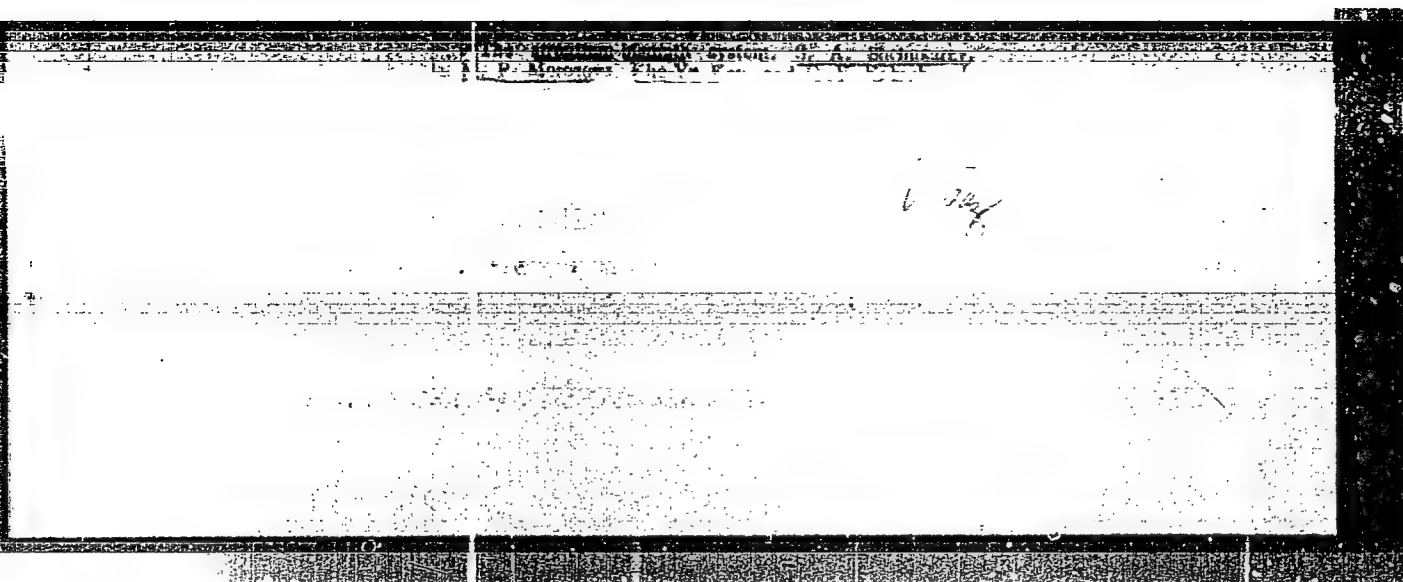
KOROSH, G.V.

APPROVED FOR RELEASE: 06/19/2000

CIA-RDP86-00513R000723710011-9"

"APPROVED FOR RELEASE: 06/19/2000

CIA-RDP86-00513R000723710011-9



APPROVED FOR RELEASE: 06/19/2000

CIA-RDP86-00513R000723710011-9"



AKKASH 64

✓ Correction for the negative branch of a thermoclement.

KOKOSH G. V.

57-1-1/30

AUTHORS: Gordyakova, G. N., Kokosh, G. V.  
Sinani, S. S.

TITLE: The Investigation of Thermoelectrical Properties of  
 $\text{Bi}_2\text{Te}_3$  -  $\text{Bi}_2\text{Se}_3$  Solid Solutions (Izucheniye  
termoelektricheskikh svoystv tverdykh rastvorov  $\text{Bi}_2\text{Te}_3$  -  
 $\text{Bi}_2\text{Se}_3$ ).

PERIODICAL: Zhurnal Tekhnicheskoy Fiziki, 1958, Vol. 28, Nr 1,  
pp. 3-17 (USSR)

ABSTRACT: The purpose of this work was to find new semiconductor  
materials for thermocouples. As for the positive part of  
the thermoelement the alloy of  $\text{Sb}_2\text{Te}_3$  and  $\text{Bi}_2\text{Te}_3$  is known as  
the best at present, the authors tried to find a material  
for its negative part. In this respect  $\text{Bi}_2\text{Te}_3$  is already  
of interest. First the electrical properties of alloys of the  
 $\text{Bi}_2\text{Te}_3$  -  $\text{Bi}_2\text{Se}_3$ -system without additions were investigated.  
As basic material bismuth, tellurium and selenium were used.  
The content of basic substance in them was ~ 99,97 %. The  
predominant addition in bismuth was lead. The radiograms of  
the investigated  $\text{Bi}_2\text{Te}_3$  -  $\text{Bi}_2\text{Se}_3$  alloy showed the formation

Card 1/4

The Investigation of Thermoelectrical Properties of  
 $\text{Bi}_2\text{Te}_3$  -  $\text{Bi}_2\text{Se}_3$  Solid Solutions

57-1-1/30

solid solutions within the range of from 100 to 80% Mol  $\text{Bi}_2\text{Te}_3$  and of from 70 to 100%  $\text{Bi}_2\text{Se}_3$ . The radiogram were taken by R. A. Zvinchuk in the A. M. Yelistratov laboratory. The investigations for the electric conductivity and for the thermo-e.m.f. (electromotive force) carried out according to the compensation method show that the former gradually decreases with its distance from the basic double compounds. With a ratio close to one of

$$\frac{\text{Bi}_2\text{Te}_3}{\text{Bi}_2\text{Se}_3}$$

it is minimal. The thermo-e.m.f. curve of change shows the course characteristic for solid solutions of substances with carriers of two signs: starting from  $\text{Bi}_2\text{Te}_3$  the thermo e.m.f. is positive and increase to an alloy of 20%  $\text{Bi}_2\text{Se}_3$ , then it decreases and changes the sign at ~ 65 %  $\text{Bi}_2\text{Te}_3$ , and then stays negative to pure  $\text{Bi}_2\text{Se}_3$ . The authors stated that a small surplus of tellurium and selenium transform the  $\text{Bi}_2\text{Te}_3$ -rich alloys into electron-alloys.

Card 2/4

The Investigation of Thermoelectrical Properties of  
 $\text{Bi}_2\text{Te}_3$  -  $\text{Bi}_2\text{Se}_3$  Solid Solutions

57-1-1/30

The further investigations concerned the effect of the additions on a 80 %  $\text{Bi}_2\text{Te}_3$  and 20%  $\text{Bi}_2\text{Se}_3$  containing solid solution. As additions served elements as well as compounds. The authors show that of the simple substances the elements of the 2nd, 3th, 4th, 5th and 8th group of the periodic system exercise an effect of acceptors, while halide, copper, silver, tellurium and selenium exercise that of donors. The alloys of the p-type are characterized by low movability values as well as by  $\alpha^2\sigma$ . The alloys of the n-type were obtained with sufficiently high indices for practical use. The best thermoelectrical properties were obtained with an addition of halides of the first group of the elementary system of with element-copper. The Z-values of the samples with optimal composition reached  $2.5 \cdot 10^{-3}$  degree<sup>-1</sup>.  $\alpha$  - the thermo-e.m.f.,  $\gamma$  - the thermal conductivity,  $Z = \frac{\alpha^2\sigma}{\gamma}$ . The investigation of the effect of compensated additions showed that the increase to be expected of  $\alpha$  did not occur. With samples the same concentration of carriers,

Card 3/4

The Investigation of Thermoelectrical Properties of  
 $\text{Bi}_2\text{Te}_3$  -  $\text{Bi}_2\text{Se}_3$  Solid Solutions

57-1-1/30

with or without compensation additions, the thermo-e.m.f. remained practically the same.

The authors were advised by L. S. Stil'bans and A. V. Ioffe submitted the data on the thermal conductivity of the investigated solutions.

There are 14 figures, 4 tables, and 14 references, 9 of which are Slavic.

ASSOCIATION: Institute for Semiconductors AN USSR, Leningrad (Institut poluprovodnikov AN SSSR Leningrad)

SUBMITTED: September 27, 1957

AVAILABLE: Library of Congress

Card 4/4

81626  
S/181/60/002/06/14/050  
B122/B063

24.7600  
AUTHORS:

Kokosh, G. V., Sinani, S. S.

TITLE:

Thermoelectric Properties of Alloys of the Pseudobinary  
System  $Sb_2Te_3$  -  $Bi_2Te_3$

PERIODICAL: Fizika tverdogo tela, 1960, Vol. 2, No. 6, pp. 1118 - 1124

TEXT: The present paper describes the effect of changes in concentration and various impurities of the system  $Sb_2Te_3$  -  $Bi_2Te_3$  upon its electrical conductivity  $\sigma$  and thermoelectromotive force  $\alpha$ . The amount of the individual components of the specimens was systematically changed by a shift of the stoichiometry. A preliminary examination and a discussion of the Bi-Te and Sb-Te phase diagrams by means of data supplied by N. K. Abrikosov, L. V. Poretskaya, and I. V. Ivanova (Refs. 2 and 4) has shown that, besides  $Bi_2Te_3$ , also  $BiTe$ ,  $Bi_2Te$ , and  $Bi_{14}Te_6$  may be present in the system Bi-Te. The two systems have some features in common but also characteristic differences. The two compounds crystallize out in the lattice with stoichio-

Card 1/4

Thermoelectric Properties of Alloys of the  
Pseudobinary System  $\text{Sb}_2\text{Te}_3$  -  $\text{Bi}_2\text{Te}_3$

81626  
S/181/60/002/06/14/050  
B122/B063

metrically insufficient quantities of Te, but this is more distinctly marked in the case of  $\text{Sb}_2\text{Te}_3$ . Figs. 1 and 2 show the effect of annealing and pressing of the specimens on  $\alpha$  and  $\sigma$ , depending on their concentration. Annealing for a long time (15 days) increased the p-type thermoelectromotive force of specimens enriched with  $\text{Sb}_2\text{Te}_3$  and the n-type thermoelectromotive force of specimens enriched with  $\text{Bi}_2\text{Te}_3$ . The change in  $\alpha$  at a ratio of  $\text{Bi}_2\text{Te}_3$  :  $\text{Sb}_2\text{Te}_3$  = 2:1 indicated the beginning of a reorientation in these specimens. Similar observations by S. V. Ayrapetyants and B. A. Yefimova (Ref. 5) are mentioned. The  $\alpha$ -curves exhibited the mixed p- and n-type which is characteristic of solid solutions. In order to explain the considerable rise of  $\alpha$  on long annealing, the authors examined the distribution curve of  $\alpha$  at different compositions (Fig. 3) as well as the course of the  $\alpha$ -curve with shifted stoichiometry as dependent on the admixtures of donors and acceptors (Fig. 4). It is assumed that tellurium penetrates into the lattice when the specimens are hot-pressed and especially when they are annealed. Though this also leads to a decrease in the hole concentration of the system enriched with  $\text{Sb}_2\text{Te}_3$ , the p-type thermoelectromotive force

✓

Card 2/4

Thermoelectric Properties of Alloys of the  
Pseudobinary System  $Sb_2Te_3 - Bi_2Te_3$

81626

S/181/60/002/06/14/050  
B122/R063

nevertheless rises since  $Sb_2Te_3$  has p-type conductivity, whereas the thermoelectromotive force already existing in the specimens enriched with  $Bi_2Te_3$  is increased by the addition of electron-emitting Te. The thermoelectric properties of the system are obtained from Figs. 3 and 4 for any concentration ratio. Next, the authors examine the effect of impurities on the said properties of the system with a change in its composition. The authors performed three series of experiments using pure Bi and 1) Sb of the type Cy-0 (Su-0) with Te No. 2; 2) Sb: Cy-0 (Su-0), Te No. 3; 3) Sb: Cy-100 (Su-000), Te No. 1. Analytical data on substances obtained by D. M. Shvarts are listed in Tables 1 and 2. The negativity of  $\alpha$  of the alloys in the region of 50 - 100 %  $Bi_2Te_3$  increases with increasing purity.

The maximum of the positive  $\alpha$  was shifted with increasing impurity concentration toward the side of higher  $Bi_2Te_3$  content. The impurities increase their electrical conductivity. The maximum of the positive thermoelectromotive force could be increased when no impurities were added. As was shown by A. V. Ioffe, the parts with minimum heat conductivity and maximum  $\alpha$  coincide (Fig. 8). There are 8 figures, 3 tables, and 5 references:  
4 Soviet.  
Card 3/4

IX



81626

Thermoelectric Properties of Alloys of the  
Pseudobinary System  $\text{Sb}_2\text{Te}_3$  -  $\text{Bi}_2\text{Te}_3$

S/181/60/002/06/14/050  
B122/B063

ASSOCIATION: Institut poluprovodnikov AN SSSR Leningrad  
(Institute of Semiconductors of the AS USSR, Leningrad)

SUBMITTED: November 3, 1959

Card 4/4

✓

MIKHAYLIK, P. (Sukhumi); KIN, P. (Kiyev); KOKOSHA, A. (Dnepropetrovsk);  
SOPOV, V. (Use-Tobe, Alma-Atinskaya obl.); TSIRKUNOV, M. (TSelinnyy kray);  
KHODIN, I. (Brestskaya obl.); MOS'PAN, G. (Lugansk); KHRAPYLIN, M.  
(Novosibirsk)

About good people. Pozh.delo 9 no.3:29 Mr '63.  
(Firemen)

(MIRA 16:4)

KOKOSHA, V. P.

KOKOSHA, V. P.- "Investigation of the Working Process of a High-speed Piston Compressor of Low Capacity." Min of Higher Education USSR, Khar'kov Polytechnic Inst imeni V. I. Lenin, Khar'kov, 1955 (Dissertations For Degree of Candidate of Technical Sciences)

SO: Knizhnaya Letonis' No. 26, June 1955, Moscow

KOKOSHA, V.P.; BORKOVSKIY, V.V.

Multipoint measuring bridge for wire data recorders. Sber. trud.  
Lab. prebl. bystr. mash. no.5:187-194 '55. (MLRA 9:2)  
(Strains and stresses--Measurement) (Electric measurements)

RAZMADZE, A.N.; KOKOSHASHVILI, R.I.; MELASHVILI, Yu.K.; CHITAYSHVILI, Z.A.

New type of standardized single-circuit 110 kv overhead power  
transmission line tower for mountainous areas. Trudy GPI [Grus.]  
no.1:153-159 '63. (MIRA 18:2)

KOZLOV, Aleksey Yefremovich; RATOVSIIY, Pinkhus Mendeleovich;  
~~KOKOSHEV, Vasilii Grigor'yevich; PETROV, Georgiy~~  
Yefremovich; POSTERNYAK, Ye.P., inzh., red.; TELYASHOV,  
R.Kh., red.izd-va; GVIRTIS, V.L., tekhn. red.

[New cutting-tool holding heads for lathes] Novye reztse-  
dershatel'nye golovki k tokarnym stankam. Leningrad,  
1963. 12 p. (Leningradskii dom nauchno-tekhnicheskoi pro-  
pagandy. Obmen peredovym opytom. Seriya: Mekhanicheskaya  
obrabotka metallov, no.15) (MIRA 17:1)

KOZLOV, Aleksey Yefimovich; KOKOSHEV, Vasily Grigor'yevich;  
PETROV, Georgiy Yefimovich; RATOVSKIY, Petr Mikhaylovich;  
KOGAN, I.L., red.

[Manufacture of diaphragms and bellows from beryllium  
bronze] Izgotovlenie membran i sil'fonov iz berillievoi  
bronzy. Leningrad, 1964. 17 p. (Leningradskii dom nauchno-  
tekhnicheskoi propagandy. Obmen передовым опытом. Seriya:  
Goriachaia i kholodnaia obrabotka metallov davleniem, no.2)  
(MIRA 17:7)

KOKOSHINSKAYA, V.I., dotsent; BOGACHEVA, V.S.

Hygienic properties of all-synthetic fabrics made from high-bulk polyacrylonitrile yarn. Tekst. prom. 25 no.5:13-15 My '65.  
(MIRA 18:5)

1. Leningradskiy institut sovetskoy trgovli imeni F. Engel'sa (for Kokoshinskaya). 2. Zaveduyushchiy laboratoriyey fabriki "Lenskno" (for Bogacheva).



CORELIK, L.M., kand.filolog,nauk; KOKOSHINSKAYA, V.I., kand.tekhn.nauk

Present-day textile terminology; discussion. Tekst.prom. 22  
no.1:78-81 Ja '62. (MIRA 15:2)

1. Leningradskiy institut sovetskoy trgovli imeni F.Engel'sa.  
(Textile fabrics--Terminology)

KOKOSHINSKAYA, V.I., kand.tekhn.nauk

Damages of jute and kenaf fibers caused by micro-organisms.  
Izv.vys.ucheb.zav.; tekhn.prom. no.5:40-47 '61. (MIRA 14:12)

1. Leningradskiy institut sovetskoy trgovli imeni Engel'sa.  
Rekomendovana kafedroy tovarovedeniya promyshlennykh tovarov.  
(Textile fibers)  
(Micro-organisms)

KOKOSHINSKAYA, V.I., kand.tekhn.nauk, starshiy nauchnyy sotrudnik

Quality of hemp ropes. Tekstilprom. 23 no.5:50-52 My '83.  
(MIRA 16:5)

1. Leningradskiy institut sovetskoy trgovli imeni Engel'sa (LIST).  
(Rope--Testing)

KOKOSHINSKAYA, V.I., dotsent, kand. tekhn. nauk

Resistance of synthetic fibers to attack by micro-organisms.  
Tekst. prom. 24 no.8:19-22 Ag '64. (MIRA 17:10)

1. Leningradskiy institut sovetskoy trgovli imeni V. Engel'sa.

KOKOSHINSKAYA, V.I., kand.tekhn.nauk, dotsent; SHMANEVA, R.N., kand.tekhn.  
nauk, assistant; PEREPELKINA, M.D.; SHCHERBAKOVA, M.N.;  
BOGACHEVA, V.S.

Properties of half-woolen nonwoven fabrics. Tekst.prom. 25  
no.11:52-56 N '65.

(MIRA 18:12)

1. Kafedra tovarovedeniya promyshlennykh tovarov Leningradskogo instituta sovetskoy trgovli imeni Engel'sa (for Kokoshinskaya).
2. Kafedra tovarovedeniya Leningradskogo instituta sovetskoy trgovli imeni Engel'sa (for Shmaneva). 3. Nachal'nik otdela netkanykh materialov Leningradskogo nauchno-issledovatel'skogo instituta tekstil'noy promyshlennosti (for Perepelkina).
4. Rukovoditel' gruppy otdela netkanykh materialov Leningradskogo nauchno-issledovatel'skogo instituta tekstil'noy promyshlennosti (for Shcherbakova). 5. Nachal'nik tekhnicheskogo otdela fabriki "Lensukno" Leningrad (for Bogacheva).

KOKOSHINSKIY, I.G.

3618. KOKOSHINSKIY, I.G. Bor'ba S. Prigoraniyem Porchinyevykh Kolyesh  
Dvigat'yel'nyy Tyetlovozov Tel I. Te 2. M., Transzhelydorizdat, 1954. 12s.  
S Chyert. 21sm (Vsyeyoyuz Nauchissled. In-t zh-D Transporta. Inform  
Pis'mo No. 317). 1,000eks. Byespl.-Ma Obl. Avt. Nye Ukazany-(54-14151 zh)  
621.431.72-242 + 621.887

SO: Knizhnaya Letopis', Vol. 3, 1955

KOKOSHINSKIY, I.O.; TSARNIADSKIY, V.A.; GRUKOV, K.A.

Controlling sticking of piston rings in the D50 engine. Trudy  
TSNII MPS no 87:133-161 '54. (MIRA 8:3)  
(Diesel locomotives)

Kokoshinskiy, I.G.

POYDA, Afanasiy Arsent'yevich; ~~KOKOSHINSKIY, Ivan Grigor'eyvich~~; GALANOVA,  
M.S., inzh., red.; KETROV, P.A., tekhn.red.

[Working principle and repair fo diesel locomotives] Ustroistvo i  
remont teplovozov. Moskva, Gos.transp.zhel-dor. izd-vo. Pt.1.

[Diesels, auxiliary equipment and cars] Diesel', vspomogatel'noe  
oborudovanie i ekipazh. 1957. 490 p. (MIRA 11:2)

(Diesel locomotives--Maintenance and repair)



FUFHYANSKIY, N.A., doktor tekhn.nauk, prof.; GURNEVICH, A.N., kand.tekhn.  
nauk; KOKOSHINSKIY, I.G., kand.tekhn.nauk

Operation of fuel system components of diesel locomotive engines.  
Elek. 1 topl.tiaga 3 no.2:30-32 F '59. (MIRA 12:4)  
(Diesel locomotives—Equipment and supplies)  
(Fuel pumps)

KOKOSHINSKIY, I.G., kand.tekhn.nauk

Tightening of the sleeve linings of the 2D100 diesel engine. Trudy  
TSNII MPS no.230:57-66 '62. (MIRA 15:7)  
(Diesel locomotives) (Diesel engines)

BABAYEV, N.K., inzh.; KOKOSHINSKIY, I.G., kand.tekhn.nauk

Restoration of tension in the bushings of the bearings of a diesel  
engine. Elek.i tepl.tiaga 7 no.1:20-21 Ja '63. (MIRA 16:2)  
(Diesel locomotives)

POYDA, A.A.; KOKOSHINSKIY, I.G.; TITOV, A.N., retsenzent; MOISEYEV,  
G.A., retsenzent; KHARLANOV, P.G., retsenzent; KESAREV,  
A.P., retsenzent; RUKAVISHNIKOV, Yu.A., retsenzent;  
MEDVEDEV, G.G., retsenzent; PALKIN, A.P., retsenzent;  
BOL'SHAKOV, A.S., retsenzent; KHITROVA, N.A., .tekhn.red.

[Mechanical equipment of diesel locomotives] Mekhanicheskoe  
oborudovanie teplovozov. Moskva, Transzheldorizdat, 1963.  
463 p. (MIRA 17:2)

KOKOSHKA, V.

Forging .

Economizing metal in the forging shop. Za ekon. mat. No. 1, 1952.

Monthly List of Russian Accessions, Library of Congress, December 1952. Unclassified.



1. VISHTAK, S.; KOKOSHKA, V.
2. USSR (600)
4. Women as Farmers
7. Towards the sunny heights of communism. Mol. kolkh., 20, No. 1, 1953.
9. Monthly List of Russian Accessions, Library of Congress, \_\_\_\_\_ 1953, Uncl.

KOKOSHKA, Vasilii, kuznets.

[Let's economize on metal] *Ekonomia metall* [Moskva] Profizdat,  
1953. 50 p. (MLRA 6:12)

(Automobile industry)

1. Moskovskiy avtomobil'nyy zavod imeni I.V.Stalina.



SHIVACHEVA, S.; STOYANOV, S.; KOLAROVA, D.; KOKOSHKAROVA, A.

Experience in preventing seizures in schizophrenia patients in remission. Zhur. nevr. i psikh. 65 no.8:1258-1265 '65.

(MIRA 18:8)

1. Psikhiatriceskaya i laboratorno-eksperimental'naya sekti  
Nauchno-issledovatel'skogo instituta nevrologii i psikhatrii  
(direktor - prof. G. Ganev) i kafedra psikhatrii (zaveduyushchiy -  
prof. Ye. Sharankov) Instituta spetsializatsii i usovershenstvo-  
vaniya vrachey, Sofiya.

KOKOSHIN, A.A., inzhener.

Making reinforced concrete casings for electric power line poles.  
Rats. i izobr.predl.v stroi. no.120:29-31 '55. (MIRA 9:7)  
(Electric lines--Poles) (Precast concrete)

ALEYNIKOV, G.I., kand. tekhn. nauk; ZENKEVICH, Yu.V., kand. tekhn. nauk;  
GUREVICH, S.A., inzh.; KOKOSHKIN, I.A., inzh.

Results of thermochemical tests of the PK-12 boiler and of  
observations on the water system of super-high parameter units  
under operating conditions. Energomashinostroyeniye 7 no.3:1-6  
Mr. '61. (MIRA 16:8)

(Boilers--Testing)

KOKOSHIN, I. V.

USSR/Human and Animal Physiology - The Nervous System.

V-10

Abs Jour : Ref Zhur - Biol., No 2, 1958, 9056

Author : I.V. Kokoshkin

Inst : The Leningrad State Institute of Pediatrics.

Title : The Mechanism of Differentiation Inhibition and Conditioned Inhibition.

Orig Pub : Uch. zap. Leningr. gos. med. in-ta, 1956, 113, 101-118

Abstract : The production of conditioned inhibition in dogs was accomplished with much greater difficulty than the formation of differentiation, and the intensity of the inhibitory process was in this case considerably less. The basis of the mechanism of conditioned inhibition rests first on the synthesis of stimuli and then on their analysis. Differentiation inhibition begins immediately with an analysis of the stimulus. The alteration of conditioned

Card 1/2

KOKOSHKIN, P.A., Cand Tech Sci -- (diss) "Investigation of  
the basic elements and a method for the engineering calcu-  
lation of rectifiers for wire-line units," Moscow, 1960, 15 pp  
(Moscow Electrotechnical Institute of Communications) (EL, 34-60, 122)

KOKOSHKIN, P.A.

Rectifying equipment for the power supply of rural telephone networks. Vest. svyazi 25 no.4:5-8 Ap '65.

(MIRA 18:6)

1. Nachal'nik energootdela Tsentral'nogo konstruktorskogo byuro Ministerstva svyazi SSSR.

KOKOSHKIN, P.A.

Dispatcher controlled signal system for postal processes at  
large post offices. Vest. aviazii 21 no.4:26-28 Ap '61.  
(MIRA 14:6)

1. Nachal'nik otдела energetiki Tsentral'nogo konstruktorskogo  
byuro Ministerstva svyazi SSSR.  
(Postal service--Intercommunication systems)

PHASE I BOOK EXPLOITATION

SOV/4823

Kokoshkin, Pavel Aleksandrovich, and Lev Solomonovich Golubev

Novyye avtomatizirovannyye vypryamitel'nyye ustroystva dlya elektropitaniya apparatury provodnoy svyazi; informatsionnyy sbornik (New Automated Rectifier Devices for the Power Supply of Wire-Communication Apparatus; Information Handbook) Moscow, Svyaz'izdat, 1960. 73 p. (Series: Tekhnika svyazi) 12,500 copies printed. Errata slip inserted.

Sponsoring Agencies: Tekhnicheskoye upravleniye Ministerstva svyazi SSSR; Tsentral'noye konstruktorskoye byuro Ministerstva svyazi SSSR.

Resp. Ed.: V.N. Kuleshov; Tech. Ed. S.F. Karabilova; Ed.: N.M. Kondrashina.

PURPOSE: This handbook is intended for technical personnel concerned with the automation of the power supply in wire-communication apparatus.

COVERAGE: The handbook contains a short description of the designs and circuits of the new automated VU rectifier devices developed by the Tsentral'noye konstruktorskoye byuro Ministerstva svyazi SSSR (Central Design Office of the

Card 1/5

Card 2/5



KAZARINOV, Ivan Alekseyevich; KOKOSHNIK, Pavel Aleksandrovich; KULESHOV,  
V.N., otv.red.; KONDRASHINA, N.M., red.; MARKUCH, K.G., tekhn.red.

[Design of power supply devices for wire-communication enterprises]  
Proektirovaniye elektropitalushchikh ustanovok predpriyatii pro-  
vodnoi svyazi. Moskva, Gos.isd-vo lit-ry po voprosam svyazi i  
radio, 1960. 399 p. (MIRA 14:3)

(Electric power supply for apparatus)  
(Telegraph) (Telephone)

BOVKUN, Viktor Georgiyevich; KAZARINOV, Ivan Alekseyevich; KOKOSHKIN, Pavel Aleksandrovich; LYUBSKIY, Gennadiy Severianovich; MEDOVAR, Anatoliy Isayevich; PETROV, Viktor Vasil'yevich; PIONTKOVSKIY, Bronislav Aleksandrovich; SERIYAKOV, Nikolay Ivanovich; ELINSON, Mikhail Mikhaylovich; SERGEYCHUK, K.Ya., red.; GRIGOR'YEV, B.S., red.; FORTUSHENKO, A.D., red.; BUSANKINA, N.G., red.; SHEFER, G.I., tekhn. red.

[Engineering manual on electric communications; electric equipment] Inzhenerno-tekhnicheskii spravochnik po elektrosvyazi; elektroustanovki. Moskva, Gos. izd-vo lit-ry po voprosam svyazi i radio, 1962. 671 p. (MIRA 15:6)

(Telecommunication--Handbooks, manuals, etc.)

(Electric engineering--Handbooks, manuals, etc.)

S/137/62/000/002/057/14  
A006/A101

AUTHOR: Kokoshkin, V. A.

TITLE: Quality control of the homogeneity of AlSb crystals

PERIODICAL: Referativnyi zhurnal. Metallurgiya, no. 2, 1962, 38 - 39, abstract 20298. (V sb.: "Vopr. metallurgii i fiz. poluprovodnikov", Moscow, AN SSSR, 134 - 137)

TEXT: The author studied the non-homogeneous distribution of admixtures in AlSb n- and p-type crystals, containing according to data of spectral analyses Mg, Si, Fe, Cu, As, Au and Pb (about  $10^{-4}\%$  each) and alloyed with elements of groups II and VI of the periodic system. The study was made by means of 1) visual inspection of crystals for translucent depth with the aid of an infrared introscope sensitive to a wavelength range of  $\leq 1.3 \mu$ ; 2) electrolytic deposition of Ag on the polished surface of the specimen; 3) etching of the specimens in a HCl-HNO<sub>3</sub> mixture; 4) observation of changes in volt-ampere characteristics and the thermo-emf sign of the metallic probe. Investigations by method 1 showed the monotonous change of general translucence over the ingot length, and also periodically located dark transverse bands. The frequency of the regular alternation

Card 1/2

S/509/62/000/011/006/019  
E071/E351

AUTHORS: Kokoshkin, V.A. and Shen, Tyan'- khuey  
TITLE: Ohmic contacts for aluminum antimonide  
SOURCE: Akademiya nauk SSSR. Institut metallurgii. Trudy.  
no. 11. Moscow, 1962. Metallurgiya, metallovedeniye,  
fiziko-khimicheskiye metody issledovaniya. 109-113

TEXT: Two methods of metal deposition from solutions onto a surface of aluminum antimonide, in order to produce ohmic contacts, were investigated. Chemical deposition of nickel from an aqueous solution, using sodium hyposulphite as the reducing agent, gave the best results. Subsequent soldering of the usual tin terminal permits the production of ohmic low-resistance p- and n-type contacts for aluminum antimonide. The rectification appears only on the contacts of a high-resistance material of the n-type, or on a compensated material. Electrodeposition of the metal from nonaqueous solutions was found to be less effective. Low-resistance ohmic contacts were obtained only on a low-resistance material of the p-type by electrodeposition of silver from silver nitrate solutions in pyridine. Contacts suitable for the measurements of

Card 1/2

S/509/62/000/011/006/019  
E071/E351

Ohmic contacts for ....

the specific resistance and of the Hall effect in aluminum antimonide of any resistance and any type of conductivity, at temperatures near the ambient, can be produced by either method. Nickel contacts with soldered tin terminals can be used for the above measurements over a wide temperature range and, in particular, at liquid-nitrogen temperatures. The difficulties of producing electric contacts on aluminum antimonide which are suitable for the above measurements are thought to be due to the presence of a hydroxide film, which is difficult to remove, and with the surface layers of the material itself (possibly the formation of double-charge layers). There are 1 figure and 1 table.

Card 2/2

S/509/62/000/011/007/019  
E021/E351

**AUTHOR:** Kokoshkin, V.A.

**TITLE:** A method of measuring microhardness on anisotropic crystals

**SOURCE:** Akademiya nauk SSSR. Institut metallurgii. Trudy. no. 11. Moscow, 1962. Metallurgiya, metallovedeniye, fiziko-khimicheskiye metody issledovaniya. 114 - 119

**TEXT:** The size and shape of indentations produced by a hardness test depend not only on the load but also on the distribution of the load in relation to the slip planes. Tips of special form have therefore been developed to enable the dimensions of the indentation to be related to definite crystal planes. It is, in fact, easier to correlate the dimensions with the slip planes as these planes play the main role in the development of deformation of anisotropic crystalline substances. Examples quoted are tips for use with face-centered cubic-lattice materials (many metals) and diamond-type lattice materials (semiconductors such as germanium and silicon). The dimensions of the tips for tests on the three basic crystallographic planes with the tip faces parallel

Card 1/2

A method of ....

S/509/62/000/011/007/019  
E021/E351

to the slip planes are:

Plane of measurement	no. of faces of pyramid	Angle between plane and face	Angle between opposite faces of pyramid
(100)	4	54°46'	70°28'
(110)	4	36°14'	109°32'
(111)	3	70°28'	-

The special tip shapes ensure the closest correspondence between the tip and the indentation. They also considerably diminish the errors of measurement due to distortion in shape of the indentation, crack formation, etc. and so increase the reproducibility of the method. The increased accuracy considerably widens the possibility of the method. In particular, it is possible to carry out a more detailed study of the anisotropy of crystalline substances compared with the conventional method. The possible application of the method to the investigation of the mechanical properties of single crystals with a low dislocation density merits special attention. There are 2 figures and 1 table.  
Card 2/2

S/509/62/000/011/008/019  
E021/E351

AUTHOR: Kokoshkin, V. A.

TITLE: Method of determining the crystallographic orientation of crystals from microhardness measurements

SOURCE: Akademiya nauk SSSR. Institut metallurgii. Trudy. no. 11. Moscow, 1962. Metallurgiya, metallovedeniye, fiziko-khimicheskiye metody issledovaniya. 120 - 123

TEXT: It is known that during microhardness determinations of crystalline substances by slow indentation with a diamond pyramid the substance is plastically deformed. In general, the mechanical properties of crystals are anisotropic due to their crystalline anisotropy. Microhardness results thus depend, in general, on the shape of the diamond tip and on its orientation towards a given crystallographic plane of a substance. If the shape of the tip and its orientation on the crystal plane conform to the crystal lattice and the slip planes, the microhardness results are no longer fortuitous but definite. When the orientation of the crystal planes is unknown, the size and shape  
Card 1/2



Method of determining ....

S/509/62/000/011/008/019  
E021/E351

of the indentation obtained, using the same load at various angles of rotation of the tip about its axis, will depend on orientation. This provides a simple method for determining the crystallographic orientation using pyramid tips with shapes conforming to the crystal lattice and its slip planes. An example is given showing the current shapes of the tips used for a face-centered cubic lattice and a diamond-type lattice. The orientation of a known plane of any anisotropic crystal with sufficiently low symmetry of the lattice can be determined. The accuracy of the method decreases with increase in symmetry. It is shown that the orientation of an unknown plane can also be determined but only with limited accuracy. The orientation of a single crystal can thus be found by making indentations with the specially-shaped tips on three planes, two of which are formed by rotation of one about any axis lying in this plane at an angle of about  $40^\circ$  at one and the other side.

Card 2/2

Investigation of the kinetic characteristics of highly doped indium antimonide. V. A. Kokoshkin (10 minutes).

Synthesis, doping, and preparation of single crystals of gallium arsenide. A. P. Izergin, A. G. Grizor'yeva, V. N. Chernigovskaya, G. M. Ikonnikova.

Crystallization of gallium arsenide under different pressures of arsenic vapor. S. S. Klubkov, V. A. Celivanova, G. M. Ikonnikova.

Influence of impurities on the electrical properties of gallium arsenide. M. A. Krivov, Ye. V. Malisova, C. V. Malyanov.  
(Presented by M. A. Krivov--15 minutes).

Report presented at the 3rd National Conference on Semiconductor Compounds, Kishinev, 16-21 Sept 1963

L 21720-65 ENT(m)/ENP(t)/ENP(b) IJP(c)/ASD(a)-5/AFML/BSO/SSD/RAEM(a)/  
 ESP(rs)/ESP(t) ID  
 ACCESSION NR: AP4041358 8/0048/04/028/006/0980/0984

AUTHOR: Kokoshkin, V.A.

TITLE: Hole mobility in indium antimonide doped with zinc and cadmium /Report,  
 Third All-Union Conference on Semiconductor Compounds held in Kishinev 16-21 Sep  
 1963

SOURCE: AN SSSR, Izvestiya. Seriya fizicheskaya, v.28, no6, 1964, 980-984

TOPIC TAGS: semiconductor, semiconductor research, carrier mobility, indium antimonide

ABSTRACT: Although hole mobility in InSb has been investigated by a number of authors (A.J. Strauss, J. Appl. Phys. 30, 559, 1959; K.I. Vinogradova, V.V. Galavanov and D.N. Nasledov, Fiz. tverdogo tela 4, 1673, 1962 and others), the experimental results of these studies proved difficult to explain, the maximum acceptor impurity concentrations did not exceed  $(1-5) \times 10^{18} \text{ cm}^{-3}$ , and the specific nature of the impurities was not indicated. Yet concentration effects, above a certain critical impurity concentration, may be significant. Accordingly, it was deemed of interest to determine the variation of the Hall hole mobility in InSb with the impurity concentration in

Card 1/3

L 21720-65  
ACCESSION NR: AP4041358

4

the range of maximum amounts of impurities. This required a sensitive procedure and taking all possible measures to minimize chance errors. Hence in the present work there was investigated the mobility of holes in 126 different single crystal and polycrystalline specimens of InSb alloyed with zinc and cadmium in the concentration range from  $4 \times 10^{17}$  to  $20 \times 10^{20} \text{ cm}^{-3}$  and the temperature range from 34 to 293°K. The specimens were cut from ingots at right angles to the milling axis; most of the single crystal specimens were oriented so that the magnetic field was in the (111) direction. The specimens were rectangular about 1 mm thick and had a length to width ratio of at least 3. Ordinary Sn-Pb solder was used to provide the contacts. The error in determining the mobility  $u = R\sigma$  ( $R$  is the Hall constant and  $\sigma$  is the conductivity) is 10-15%. The results are presented in the form of plots in  $u$  versus Cd and Zn concentration coordinates and are compared with the theoretical curves, calculated on the basis of different effective mass and dielectric constant values. There is an appreciable scatter of the experimental points, particularly for the polycrystalline specimens. The agreement with theory for Zn doped crystals is reasonably good, but that for Cd doped InSb is poor. Possible reasons for the discrepancies are suggested and discussed. "In conclusion, I thank Prof. D.N. Nasledov and Senior Research Assistant M.S. Mirgalovskaya for their interest in the work and L.S. Bryzgalov and N.S. Gortsen for assistance in performing the measurements."

Card 2/3

L 21720-65  
ACCESSION NR: AP4041358

Orig.art.has: 3 figures and 1 table.

ASSOCIATION: none

SUBMITTED: 00

SUB CODE: SS,EM

NO REF SOV: 007

ENCL: 00

OTHER: 006

Card 3/3

X 44233-65 ENT(1)/C/ENG(1)-2 P1-4 IJP(c) 00

ACCESSION NR: AP5011928

UR/0363/65/001/003/0340/0342

AUTHOR: Miregalovskaya, M. S.; Kokoshkin, V. A.; Smirnov, V. Ya.

TITLE: Crystal face effect in doped indium antimonide

SOURCE: AN SSSR. Izvestiya. Neorganicheskiye materialy, v. 1, no. 3, 1965, 340-342

TOPIC TAGS: indium antimonide, single crystal, doped semiconductor crystal, single crystal growth, crystal face effect, impurity distribution

ABSTRACT: The face effect  $R$  in the  $\langle 111 \rangle$  growth direction of indium antimonide single crystals doped with sulfur, selenium, or zinc has been studied in order to establish a correlation between  $R$  and the concentrations of the three impurities.  $R$  was defined as the ratio  $K_a : K_b$ , where  $K_a$  and  $K_b$  are the distribution coefficients "at the crystal face," i.e. in the central region of the crystal where an impurity incorporated by tangential growth of the face, and "beyond the face," i.e. in the peripheral region of normal incorporations of an impurity. The crystals were grown by the Czochralski technique

Card 1/3

L 44133-65

ACCESSION NR: AP5011928

under standard conditions. The average carrier (impurity) concentrations "beyond the face," ( $N_b$ ), as determined from the experimental Hall constant at liquid nitrogen temperature, were in the  $(1-4) \times 10^{17} \text{ cm}^{-3}$  range for Se and S and in the  $(0.1-3) \times 10^{19} \text{ cm}^{-3}$  range for Zn. The  $K_a : K_b$  ratio was assumed to be equal to the  $(N_a : N_b)_a$  ratio, where  $N_a$  and  $N_b$  are the carrier concentrations "at" and "beyond the face" of preferential growth, and  $\alpha$  is the Seebeck power. The  $\alpha$  values were measured by means of hot probe equidistant points along the diameters of polished cross sections cut from a single crystal. Thus, the ratios  $\alpha_b : \alpha_a$  were established and  $(N_a : N_b)_a$  ratios, i.e., were calculated on the basis of the  $\alpha(r)$  dependence established by calibration. The experimental  $(N_a : N_b)_a$  data were found to be in good agreement with the previously published data for R(111). It was shown that: 1) R for a given impurity varied significantly along the entire length of the crystal as the average impurity concentration  $N$  increased or decreased even slightly; and 2) for impurities with  $K_a < K_b$  (S, Se) R decreased and for impurities with  $K_a > K_b$  (Zn) R was nearly constant with increasing  $N$ . The concentration dependence of R(111) orig. ref. has been reported.

Card 2/3

2 44143-65

ACCESSION NR: AP5011928

INSTITUTION: Institut metallurgii M. A. A. Baykova (Institut metallurgii M. A. A. Baykova)

SUBMITTED: 20Sep64

ENCL: 00

SUB CODE: SS

NO REF SOV: 005

OTHER: 004

ATD PRESS: 3246

Card 3/3



L 58713-65 ENT(1)/T/EEC(b)-2 P1-4 IJP(e) 00

ACCESSION NR- AP5010591

IR/0363/85/001/005/0668/0674  
46. 682'861-162. 2

AUTHOR: Kokoashkin, V. A.; Mirgalovskaya, M. S.; Bezborodova, V. M.

TITLE: The degree of homogeneity of doped indium antimonide crystals

SOURCE: AN SSSR. Izvestiya. Neorganicheskiye materialy, v. 1, no. 5, 1965, 663-674

TOPIC TAGS: indium antimonide, crystal growth, zinc doping, cadmium doping, thermoelectromotive force, Hall mobility

ABSTRACT: By using the method of thermo-emf measurements, the authors attempted to determine the inhomogeneities which may arise in indium antimonide crystals doped with acceptor impurities. It was found that indium antimonide ingots doped with zinc as well as cadmium up to concentrations of  $4 \times 10^{17} - 2 \times 10^{18} \text{ cm}^{-3}$ , prepared by the Czochralski method at  $v = (0.7-1.3) \cdot 10^{-5} \text{ m/sec}$  and  $n_1 = 0.8-1 \text{ rps}$ , may have appreciable inhomogeneities in the longitudinal and transverse distribution of the impurity. Variations in the distribution of the thermo-emf may reach + 20% in some parts of the ingots. Doping with zinc produces a more homogeneous material. An ingot containing zinc is relatively homogeneous over most of its body, and the variations in distribution  $\alpha$  are + (4-5)%. The nonuniform layered trapping of zinc and cadmium during crystallization is primarily

Card 1/2

L 58713-65

ACCESSION NR: AP5016581

3

helical in character, and is determined by the conditions of growth. A 50-100% increase in growth rate (to  $1.3 \times 10^{-5}$  m/sec) impairs the homogeneity of the ingots. The ob-  
servations significantly affect the Hall mobility. A definite correlation was  
established between the change in the degree of homogeneity of the samples with a  
concentration of  $10^{18}$  cm $^{-3}$  and the deviation of the experimental value of the  
mobility from the calculated value. The authors thank Dr. I. S. Ryzgalov for assistance in the experimental work. " Orig. art. has: 6 figures and  
1 table.

ASSOCIATION: Institut metallurgii im. A. A. Baykova (Institute of Metallurgy)

SUBMITTED: 27Mar64

ENCL: 00

SUB CODE: IC

NO REF SOV: 008

OTHER: 008

*dm*  
Card 2/2

EXT(1)/EMP(e)/EPA(t)-2/EXT(n)/EXT(1)/EPT(n)-2/ET(t)/T/EPA(n)-2/ETP(t)/  
 b.10/ET-7/Pd/Pu-1 IF(e)-AD AT-4H UR/0032/65/031/004/0461/0463  
 ACCESSION NR: AP5009917

AUTHOR: Kokoshkin, V. A.

TITLE: Investigating the uniformity of highly alloyed semiconductors with the help of a heated thermocouple probe

SOURCE: Zavodskaya laboratoriya, v. 31, no. 4, 1965, 461-463

TOPIC TAGS: thermoelectricity, semiconductor, thermocouple, indium antimony / antimony thermometer, K21/4 galvanometer

The method of measuring thermoelectromotive force (TEMF) with a  
 probe is applied to the investigation of the uniformity of  
 semiconductor specimens. The probe is heated by a  
 gas flame. The specimens are placed in a container  
 heated by springs at 400°C. The temperature at which the  
 probe is heated is 400°C.

The force pressing the probe against the specimen is 100 g.  
 Copper-constantan thermocouples are used. The thermocouple leads

Card 1/1

L 4833C-65

ACCESSION NR: AP5009917

pass through double ceramic tubes 8 which maintain a constant temperature provided by heater 9. The hood 10 diminishes the air convection. The specimen electrodes are protected by a copper shield. Absorbers 12 serve to stabilize the contacts. Temperatures and time were measured with a millivolt potentiometer and a M21/4 galvanometer. Results obtained in investigating n-type InSb are plotted on Fig. 2 on the Enclosure. Here the ordinate values indicate the temperatures on the surface of the specimen in relation to the hot probe temperature (taken as a unity), and distances between the probes are shown as the abscissa values. The most indicative results are obtained when the surface is etched. The readings are not affected by a change in the material of the platform, but show substantial irregularity when the probe is placed at the boundary of a crystalline grain. Orig. art. has: 3 figures.

ASSOCIATION: Institut metallurgii im. A. A. Baykova (Institute of Metallurgy)

SUBMITTED: 00

ENCL: 02

SUB CODE: 88, EM

NO REF SOV: 005

OTHER: 001

Card 2/4

KOKOSHKINA, A. A.

"Electrophoresis of Sympathomimetics in Nervous Diseases." Cand Med Sci,  
Crimean Medical Inst, Simferopol', 1953. (RZhBiol, No 4, Oct 54)

Survey of Scientific and Technical Dissertations Defended at USSR Higher  
Educational Institutions (10)

SO: Sum. No. 481, 5 May 55

~~SECRET~~  
KOKOSHKINA, A.A. (Simferopol')

Electrophoresis of sympathomimetin in nervous diseases. Vrach.  
delo supplement '57:84-85 (MIRA 11:3)

1. Nervnoye klinicheskoye otdeleniye oblastnoy klinicheskoy  
obl'nitsy im. Semashko i detskiy sanatoriy "Zdravnitsa"  
evpatoriyskogo kurorta (nauchnyy rukovoditel'-prof. N.N.Pyatnitskiy)

*Kokoshkina, A.A.*  
KOKOSHKINA, A.A. (Kiyev)

Administration of sympathomimetin by electrophoresis in nervous diseases. Vrach.delo supplement '57:88-89 (MIRA 11:3)

1. Pervaya fizioterapevticheskaya bol'nitsa i nervnoye otdeleniye  
bol'nitsy zavoda "Bol'shevik".  
(SYMPATHOMIMETICS) (ELECTROPHORESIS)

NIKITIN, Petr Ivanovich; ARAV, O., red.; BAKOVETSKIY, O., red.;  
DARONYAN, M., mladshiy red.; KOKOSHKINA, I., mladshiy red.;  
CHEPELEVA, O., tekhn. red.

[Principles of economics; popular textbook] Osnovy politiches-  
skoi ekonomii; popularnyi uchebnyk. 2., perer. i dop. izd.  
Moskva, Sotsekgiz, 1962. 398 p. (MIRA 15:8)  
(Economics)



STEPANENKO, Stanislav Ivanovich; SHIRYAYEV, Yu., red.; BAKOVETSKIY, O.,  
red.; KOKOSHKINA, I., mladshiy red.; CHEPELEVA, O., tekhn. red.

[Scientific and technical cooperation of socialist countries]  
Nauchno-tekhnicheskoe sotrudnichestvo sotsialisticheskikh stran.  
Moskva, Sotsekgiz, 1962. 86 p. (MIRA 15:12)  
(Communist countries--Technology--International cooperation)

NEMCHINOV, Vasil'y Sergeyevich (1894- ), laureat Gosudarstvennoy premii;  
GLIAZER, L., red.; KOKOSHKINA, I., mladshiy red.; CHEPELEVA, O.,  
tekhn. red.

[Mathematical economics methods and models] Ekonomiko-matematicheskie metody i modeli. Moskva, Sotsekgiz, 1962. 409 p.

(MIRA 16:2)

(Economics, Mathematical)

SAVCHUK, Porfiriy Osipovich; BAKOVETSKIY, O., red.; KOKOSHKINA, I.,  
mladshiy red.; NOGINA, N., tekhn. red.

[Essays in economics] Ocherki politicheskoi ekonomii. Mo-  
skva, Sotsisgiz, 1963. 422 p. (MIRA 16:10)  
(Economics)

KATS, V.I., doktor ekon. nauk; KIRICHENKO, V.N., kand. ekon. nauk;  
 IVANOV, Ye.A.; SAID-GALIYEV, K.G.; LUK'YANOV, E.B.; MUSATOVA,  
 V.A.; PLYSHEVSKIY, B.P., kand. ekon. nauk; STOMAKHIN, V.I.;  
 KARPUKHIN, D.N., kand. ekon. nauk; KIRICHENKO, N.Ya.;  
 ZHIDKOVA, M.V., kand. ekon. nauk; ANCHISHKIN, A.I.; KLINSKIY,  
 A.I., kand. ekon. nauk; SOLOV'YEV, N.S.; KLOTSVOG, P.N.;  
 VSYAKIKH, E.P.; LAGUTIN, N.S., kand. ekon. nauk; LEMESHEV, M.Ya.,  
 kand. sel'khoz.nauk; KORMNOV, Yu.F., kand. ekon. nauk; SAVIN,  
 V.A.; TEREKHOV, V.F.; KUDROV, V.M., kand. ekon. nauk; AL'TER,  
 L.B., doktor ekon. nauk, red.; KRYLOV, P.N., kand. ekon. nauk;  
 LEPINKOVA, Ye., red.; KOKOSHKINA, I., mladshiy red.; ULANOVA, L.,  
 tekhn. red.

[Growth of the social product and the proportions of the  
 national economy of the U.S.S.R.] Rost obshchestvennogo pro-  
 izvodstva i propotsii narodnogo khoziaistva SSSR. Moskva,  
 1962. 453 p. (MIRA 16:2)

(Russia--Economic policy)

AKOPOV, R.Ya., kand. ekon. nauk, dots.; BASYUK, T.L., doktor ekon. nauk, prof.; BIRMAN, A.M., doktor ekon. nauk, prof.; GRIGOR'YEV, A.Ye., doktor ekon. nauk, prof.; DOKUKIN, V.I., prof.; IKONNIKOV, V.V., prof.; KONDRASHEV, D.D., doktor ekon. nauk; KURSKIY, A.D., doktor ekon. nauk; LOKSHIN, E.Yu., doktor ekon. nauk, prof.; MALYY, I.G., kand. ekon. nauk, dots.; PERVUSHIN, S.P., kand. ekon. nauk; PLOTNIKOV, K.N., TYAPKIN, N.K., kand. ekon. nauk; FILIMONOV, N.P., kand. ekon. nauk; SHAPIYEV, K.N., doktor ekon. nauk, prof.; BAKOVETSKIY, O., red.; KOKOSHKINA, I., mladshiy red.; MOSKVINA, R., tekhn. red.

[Economics; communist means of production] Politicheskaya ekonomiya; kommunisticheskiy sposob proizvodstva. Uchebnik 2., perer. 1 dop. izd. Moskva, Sotsekgiz, 1963. 599 p.

(MIRA 16:5)

1. Chlen-korrespondent Akademii nauk SSSR (for Plotnikov).  
(Economics) (Communism)

SAMBORSKIY, Georgiy Ivanovich; LEJNIKOVA, Ye., red.; KOKOSHKINA, I.,  
mlad. red.

[Automation and specialization in U.S.S.R. industry] Avto-  
matizatsiia i spetsializatsiia v promyshlennosti SSSR. Mo-  
skva, Mysl', 1964. 214 p. (MIRA 18:1)

NEMCHINOV, V.S., akademik, red. [deceased]; Prinsipalni uchastiye:  
MIKHALEVSKIY, B.N.; MINTS, L.Ye.; SHISHANKOV, V., red.;  
KOKOSHKINA, I., mlad. red.

[Application of mathematics in economic research] Primenenie matematiki v ekonomicheskikh issledovaniyakh. Moskva, Mysl'. Vol.3. 1965. 494 p. (MIRA 18:4)

GORBUNOV, Eduard Petrovich; BAKOVETSKIY, O.D., red.; KOKOSHKINA,  
I.K., mlad. red.

[Rates, level and structure of industrial production in  
the U.S.S.R.] Tempy, uroven' i struktura promyshlennogo  
proizvodstva v SSSR. Moskva, Mysl', 1965. 186 p.  
(MIRA 18:8)



VASIL'YEV, Nikolay Vasil'yevich; LEPNIKOVA, Ye.P., red.;  
KOKOSHKINA, I.K., mlad. red.

[Specialization and zoning of farming in the U.S.S.R.]  
Spetsializatsiia i razmeshchenie sel'skokhoziaistven-  
nogo proizvodstva v SSSR. Moskva, Mysl', 1965. 452 p.  
(MIRA 18:6)

NEMCHINOV, Vasilii Sergeyevich, akademik (1894-1964); VAYNSHTEYN,  
A.L., red.; SHISHANKOV, V.S., red.; KOKOSHKINA, I.K., red.

[Economic-mathematical methods and models] Ekonomiko-matema-  
ticheskie metody i modeli. Moskva, Mysl', 1965. 477 p.  
(MIRA 18:9)

KOKOSHKO, A.

For the readers of economics literature. Vop. ekon. no. 6:146  
Je '63. (MIRA 16:6)

(Bibliography--Economics)

OZERAN, Lidiya Georgiyevna; KOKOSHKO, A.G., red.:

[Growth of the prosperity of Soviet workers; lecture on the course "Statistics" delivered for the students of the Correspondence Higher Party School attached to the Central Committee of the CPSU] Rost blagosostoiania trudiashchikhsia SSSR; lektsiia po kursu "Statistika," pročitannaia slushateliu ZVPSH pri TsK KPSS. Moskva, Izd-vo VPSH i AON, pri TsK KPSS, 1962. 62 p. (MIRA 15:10)  
(Cost and standard of living)